

Abstract

In a method for producing an SOI wafer comprising steps of implanting hydrogen ions etc. from a surface of a bond wafer 21 surface to form an ion-implanted layer 24 inside the wafer, bonding the ion-implanted bond wafer surface of the bond wafer and a surface of a base wafer 22 via an oxide film 23 or directly, and forming an SOI wafer by delaminating by heat treatment a part of the bond wafer at the ion-implanted layer by heat treatment, wherein the bond wafer is a silicon wafer consisting that consists of a silicon single crystal grown by Cheehralski-Czochralski method, which that is occupied by N region outside OSF generated in a ring shape and that has no defect region detected by Cu deposition method, is used as the bond wafer. Thereby, even in the case of forming an extremely thin SOI layer 27 such that, for example, its having a thickness is of 200 nm or less, there is provided can provide an SOI wafer which that has an excellent electric property without causing micro pits caused by acid cleaning with hydrofluoric acid etc., and in addition, can be produced without increasing the number of processes.